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Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Obsolete
Core Processor	MPC8xx
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	80MHz
Co-Processors/DSP	Communications; CPM
RAM Controllers	DRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10Mbps (4)
SATA	-
USB	-
Voltage - I/O	3.3V
Operating Temperature	0°C ~ 95°C (TA)
Security Features	-
Package / Case	357-BBGA
Supplier Device Package	357-PBGA (25x25)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mpc860enzq80d4

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Overview

1 Overview

The MPC860 power quad integrated communications controller (PowerQUICCTM) is a versatile one-chip integrated microprocessor and peripheral combination designed for a variety of controller applications. It particularly excels in communications and networking systems. The PowerQUICC unit is referred to as the MPC860 in this hardware specification.

The MPC860 implements Power ArchitectureTM technology and contains a superset of Freescale's MC68360 quad integrated communications controller (QUICC), referred to here as the QUICC, RISC communications processor module (CPM). The CPU on the MPC860 is a 32-bit core built on Power Architecture technology that incorporates memory management units (MMUs) and instruction and data caches.. The CPM from the MC68360 QUICC has been enhanced by the addition of the inter-integrated controller (I²C) channel. The memory controller has been enhanced, enabling the MPC860 to support any type of memory, including high-performance memories and new types of DRAMs. A PCMCIA socket controller supports up to two sockets. A real-time clock has also been integrated.

Table 1 shows the functionality supported by the MPC860 family.

	Cache (Kbytes)		Ethe	ernet			
Part	Instruction Cache	Data Cache	10T	10/100	ATM	scc	Reference ¹
MPC860DE	4	4	Up to 2	_	_	2	1
MPC860DT	4	4	Up to 2	1	Yes	2	1
MPC860DP	16	8	Up to 2	1	Yes	2	1
MPC860EN	4	4	Up to 4	_	_	4	1
MPC860SR	4	4	Up to 4	_	Yes	4	1
MPC860T	4	4	Up to 4	1	Yes	4	1
MPC860P	16	8	Up to 4	1	Yes	4	1
MPC855T	4	4	1	1	Yes	1	2

Table 1. MPC860 Family Functionality

Supporting documentation for these devices refers to the following:

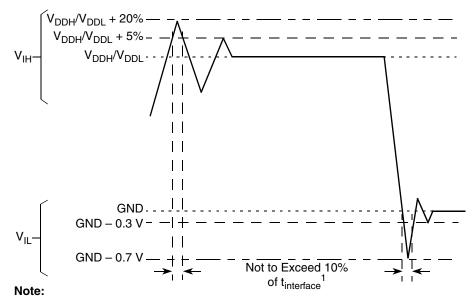
^{1.} MPC860 PowerQUICC Family User's Manual (MPC860UM, Rev. 3)

^{2.} MPC855T User's Manual (MPC855TUM, Rev. 1)



Thermal Characteristics

Figure 1 shows the undershoot and overshoot voltages at the interface of the MPC860.



^{1.} $t_{\text{interface}}$ refers to the clock period associated with the bus clock interface.

Figure 1. Undershoot/Overshoot Voltage for V_{DDH} and V_{DDL}

4 Thermal Characteristics

Table 3. Package Description

Package Designator	kage Designator Package Code (Case No.) Pack	
ZP	5050 (1103-01)	PBGA 357 25*25*0.9P1.27
ZQ/VR	5058 (1103D-02)	PBGA 357 25*25*1.2P1.27



Table 4 shows the thermal characteristics for the MPC860.

Table 4. MPC860 Thermal Resistance Data

Rating	Env	rironment	Symbol	ZP MPC860P	ZQ / VR MPC860P	Unit
Mold Compound Thickness	0.85	1.15	mm			
Junction-to-ambient ¹	Natural convection	Single-layer board (1s)	$R_{\theta JA}^2$	34	34	°C/W
		Four-layer board (2s2p)	$R_{\theta JMA}^3$	22	22	
	Airflow (200 ft/min)	Single-layer board (1s)	$R_{\theta JMA}^3$	27	27	
		Four-layer board (2s2p)	$R_{\theta JMA}^3$	18	18	
Junction-to-board 4		•	$R_{\theta JB}$	14	13	
Junction-to-case 5			$R_{\theta JC}$	6	8	
Junction-to-package top 6	Natural convection		Ψ_{JT}	2	2	

Junction temperature is a function of on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, airflow, power dissipation of other components on the board, and board thermal resistance

² Per SEMI G38-87 and JEDEC JESD51-2 with the single-layer board horizontal.

³ Per JEDEC JESD51-6 with the board horizontal.

⁴ Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.

Indicates the average thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1) with the cold plate temperature used for the case temperature. For exposed pad packages where the pad would be expected to be soldered, junction-to-case thermal resistance is a simulated value from the junction to the exposed pad without contact resistance.

⁶ Thermal characterization parameter indicating the temperature difference between the package top and the junction temperature per JEDEC JESD51-2.



Power Dissipation

5 Power Dissipation

Table 5 provides power dissipation information. The modes are 1:1, where CPU and bus speeds are equal, and 2:1, where CPU frequency is twice the bus speed.

Table 5. Power Dissipation (P_D)

Die Revision	Frequency (MHz)	Typical ¹	Maximum ²	Unit
D.4	50	656	735	mW
(1:1 mode)	66	TBD	TBD	mW
D.4	66	722	762	mW
(2:1 mode)	80	851	909	mW

¹ Typical power dissipation is measured at 3.3 V.

NOTE

Values in Table 5 represent V_{DDL} -based power dissipation and do not include I/O power dissipation over V_{DDH} . I/O power dissipation varies widely by application due to buffer current, depending on external circuitry.

6 DC Characteristics

Table 6 provides the DC electrical characteristics for the MPC860.

Table 6. DC Electrical Specifications

Characteristic	Symbol	Min	Max	Unit
Operating voltage at 40 MHz or less	V _{DDH} , V _{DDL} , V _{DDSYN}	3.0	3.6	V
	KAPWR (power-down mode)	2.0	3.6	V
	KAPWR (all other operating modes)	V _{DDH} – 0.4	V _{DDH}	V
Operating voltage greater than 40 MHz	$V_{ m DDH}, V_{ m DDL}, { m KAPWR}, \ V_{ m DDSYN}$	3.135	3.465	V
	KAPWR (power-down mode)	2.0	3.6	V
	KAPWR (all other operating modes)	V _{DDH} – 0.4	V _{DDH}	V
Input high voltage (all inputs except EXTAL and EXTCLK)	V _{IH}	2.0	5.5	V
Input low voltage ¹	V _{IL}	GND	0.8	V
EXTAL, EXTCLK input high voltage	V _{IHC}	0.7 × (V _{DDH})	V _{DDH} + 0.3	V
Input leakage current, V_{in} = 5.5 V (except TMS, \overline{TRST} , DSCK, and DSDI pins)	l _{in}	_	100	μА

² Maximum power dissipation is measured at 3.5 V.



Table 6. DC Electrical Specifications (continued)

Characteristic	Symbol	Min	Max	Unit
Input leakage current, V_{in} = 3.6 V (except TMS, \overline{TRST} , DSCK, and DSDI pins)	I _{In}	_	10	μΑ
Input leakage current, V _{in} = 0 V (except TMS, TRST, DSCK, and DSDI pins)	I _{In}	_	10	μΑ
Input capacitance ²	C _{in}	_	20	pF
Output high voltage, $I_{OH} = -2.0$ mA, $V_{DDH} = 3.0$ V (except XTAL, XFC, and open-drain pins)	V _{OH}	2.4	_	V
Output low voltage I_{OL} = 2.0 mA, CLKOUT I_{OL} = 3.2 mA 3 I_{OL} = 5.3 mA 4 I_{OL} = 7.0 mA, TXD1/PA14, TXD2/PA12 I_{OL} = 8.9 mA, TS, TA, TEA, BI, BB, HRESET, SRESET	V _{OL}	_	0.5	V

¹ V_{II} (max) for the I²C interface is 0.8 V rather than the 1.5 V as specified in the I²C standard.

² Input capacitance is periodically sampled.

³ A(0:31), TSIZ0/REG, TSIZ1, D(0:31), DP(0:3)/IRQ(3:6), RD/WR, BURST, RSV/IRQ2, IP_B(0:1)/IWP(0:1)/VFLS(0:1), IP_B2/IOIS16_B/AT2, IP_B3/IWP2/VF2, IP_B4/LWP0/VF0, IP_B5/LWP1/VF1, IP_B6/DSDI/AT0, IP_B7/PTR/AT3, RXD1/PA15, RXD2/PA13, L1TXDB/PA11, L1RXDB/PA10, L1TXDA/PA9, L1RXDA/PA8, TIN1/L1RCLKA/BRGO1/CLK1/PA7, BRGCLK1/TOUT1/CLK2/PA6, TIN2/L1TCLKA/BRGO2/CLK3/PA5, TOUT2/CLK4/PA4, TIN3/BRGO3/CLK5/PA3, BRGCLK2/L1RCLKB/TOUT3/CLK6/PA2, TIN4/BRGO4/CLK7/PA1, L1TCLKB/TOUT4/CLK8/PA0, REJCT1/SPISEL/PB31, SPICLK/PB30,SPIMOSI/PB29, BRGO4/SPIMISO/PB28, BRGO1/I2CSDA/PB27, BRGO2/I2CSCL/PB26, SMTXD1/PB25, SMRXD1/PB24, SMSYN1/SDACK1/PB23, SMSYN2/SDACK2/PB22, SMTXD2/L1CLKOB/PB21, SMRXD2/L1CLKOA/PB20, L1ST1/RTS1/PB19, L1ST2/RTS2/PB18, L1ST3/L1RQB/PB17, L1ST4/L1RQA/PB16, BRGO3/PB15, RSTRT1/PB14, L1ST1/RTS1/DREQ0/PC15, L1ST2/RTS2/DREQ1/PC14, L1ST3/L1RQB/PC13, L1ST4/L1RQA/PC12, CTS1/PC11, TGATE1/CD1/PC10, CTS2/PC9, TGATE2/CD2/PC8, SDACK2/L1TSYNCB/PC7, L1RSYNCB/PC6, SDACK1/L1TSYNCA/PC5, L1RSYNCA/PC4, PD15, PD14, PD13, PD12, PD11, PD10, PD9, PD8, PD5, PD6, PD7, PD4, PD3, MII_MDC, MII_TX_ER, MII_EN, MII_MDIO, and MII_TXD[0:3]

⁴ BDIP/GPL_B(5), BR, BG, FRZ/IRQ6, CS(0:5), CS(6)/CE(1)_B, CS(7)/CE(2)_B, WE0/BS_B0/IORD, WE1/BS_B1/IOWR, WE2/BS_B2/PCOE, WE3/BS_B3/PCWE, BS_A(0:3), GPL_A0/GPL_B0, OE/GPL_A1/GPL_B1, GPL_A(2:3)/GPL_B(2:3)/CS(2:3), UPWAITA/GPL_A4, UPWAITB/GPL_B4, GPL_A5, ALE_A, CE1_A, CE2_A, ALE_B/DSCK/AT1, OP(0:1), OP2/MODCK1/STS, OP3/MODCK2/DSDO, and BADDR(28:30)

Thermal Calculation and Measurement

7 Thermal Calculation and Measurement

For the following discussions, $P_D = (V_{DD} \times I_{DD}) + PI/O$, where PI/O is the power dissipation of the I/O drivers.

7.1 Estimation with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_I , in °C can be obtained from the equation:

$$T_I = T_A + (R_{\theta IA} \times P_D)$$

where:

 T_A = ambient temperature (°C)

 $R_{\theta,IA}$ = package junction-to-ambient thermal resistance (°C/W)

 P_D = power dissipation in package

The junction-to-ambient thermal resistance is an industry standard value which provides a quick and easy estimation of thermal performance. However, the answer is only an estimate; test cases have demonstrated that errors of a factor of two (in the quantity $T_I - T_A$) are possible.

7.2 Estimation with Junction-to-Case Thermal Resistance

Historically, the thermal resistance has frequently been expressed as the sum of a junction-to-case thermal resistance and a case-to-ambient thermal resistance:

$$R_{\theta JA} = R_{\theta JC} + R_{\theta CA}$$

where:

 $R_{\theta JA}$ = junction-to-ambient thermal resistance (°C/W)

 $R_{\theta JC}$ = junction-to-case thermal resistance (°C/W)

 $R_{\theta CA}$ = case-to-ambient thermal resistance (°C/W)

 $R_{\theta JC}$ is device related and cannot be influenced by the user. The user adjusts the thermal environment to affect the case-to-ambient thermal resistance, $R_{\theta CA}$. For instance, the user can change the airflow around the device, add a heat sink, change the mounting arrangement on the printed-circuit board, or change the thermal dissipation on the printed-circuit board surrounding the device. This thermal model is most useful for ceramic packages with heat sinks where some 90% of the heat flows through the case and the heat sink to the ambient environment. For most packages, a better model is required.

7.3 Estimation with Junction-to-Board Thermal Resistance

A simple package thermal model which has demonstrated reasonable accuracy (about 20%) is a two-resistor model consisting of a junction-to-board and a junction-to-case thermal resistance. The junction-to-case thermal resistance covers the situation where a heat sink is used or where a substantial amount of heat is dissipated from the top of the package. The junction-to-board thermal resistance describes the thermal performance when most of the heat is conducted to the printed-circuit board. It has been observed that the thermal performance of most plastic packages, especially PBGA packages, is strongly dependent on the board temperature; see Figure 2.



Table 7. Bus Operation Timings (continued)

Norma	Observatoristis	33 1	ИНz	40 [MHz	50 I	ИНz	66 I	ИНz	11!4
Num	Characteristic	Min	Max	Min	Max	Min	Max	Min	Max	Unit
B29d	WE(0:3) negated to D(0:31), DP(0:3) High-Z GPCM write access, TRLX = 1, CSNT = 1, EBDF = 0	43.45	_	35.5	_	28.00	_	20.73	_	ns
B29e	CS negated to D(0:31), DP(0:3) High-Z GPCM write access, TRLX = 1, CSNT = 1, ACS = 10, or ACS = 11, EBDF = 0	43.45		35.5	_	28.00		29.73	_	ns
B29f	WE(0:3) negated to D(0:31), DP(0:3) High-Z GPCM write access, TRLX = 0, CSNT = 1, EBDF = 1	8.86	_	6.88	_	5.00	_	3.18	_	ns
B29g	CS negated to D(0:31), DP(0:3) High-Z GPCM write access, TRLX = 0, CSNT = 1, ACS = 10, or ACS = 11, EBDF = 1	8.86		6.88		5.00		3.18		ns
B29h	WE(0:3) negated to D(0:31), DP(0:3) High-Z GPCM write access, TRLX = 1, CSNT = 1, EBDF = 1	38.67	_	31.38	_	24.50	_	17.83	_	ns
B29i	CS negated to D(0:31), DP(0:3) High-Z GPCM write access, TRLX = 1, CSNT = 1, ACS = 10, or ACS = 11, EBDF = 1	38.67		31.38	_	24.50		17.83	_	ns
B30	CS, WE(0:3) negated to A(0:31), BADDR(28:30) invalid GPCM write access ⁸	5.58	_	4.25	_	3.00	_	1.79	_	ns
B30a	WE(0:3) negated to A(0:31), BADDR(28:30) invalid GPCM, write access, TRLX = 0, CSNT = 1, CS negated to A(0:31) invalid GPCM write access, TRLX = 0, CSNT = 1 ACS = 10, or ACS = 11, EBDF = 0	13.15	_	10.50	_	8.00	_	5.58	_	ns
B30b	WE(0:3) negated to A(0:31), invalid GPCM BADDR(28:30) invalid GPCM write access, TRLX = 1, CSNT = 1. CS negated to A(0:31), Invalid GPCM, write access, TRLX = 1, CSNT = 1, ACS = 10, or ACS = 11, EBDF = 0	43.45	_	35.50	_	28.00	_	20.73	_	ns
B30c	WE(0:3) negated to A(0:31), BADDR(28:30) invalid GPCM write access, TRLX = 0, CSNT = 1. \overline{CS} negated to A(0:31) invalid GPCM write access, TRLX = 0, CSNT = 1, ACS = 10, ACS = 11, EBDF = 1	8.36		6.38	_	4.50		2.68	_	ns
B30d	WE(0:3) negated to A(0:31), BADDR(28:30) invalid GPCM write access, TRLX = 1, CSNT =1. \overline{CS} negated to A(0:31) invalid GPCM write access TRLX = 1, CSNT = 1, ACS = 10, or ACS = 11, EBDF = 1	38.67	_	31.38	_	24.50	_	17.83	_	ns
B31	CLKOUT falling edge to CS valid—as requested by control bit CST4 in the corresponding word in UPM	1.50	6.00	1.50	6.00	1.50	6.00	1.50	6.00	ns



Figure 9 provides the timing for the input data controlled by the UPM for data beats where DLT3 = 1 in the UPM RAM words. (This is only the case where data is latched on the falling edge of CLKOUT.)

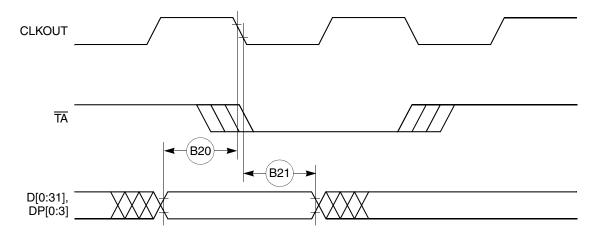


Figure 9. Input Data Timing when Controlled by UPM in the Memory Controller and DLT3 = 1

Figure 10 through Figure 13 provide the timing for the external bus read controlled by various GPCM factors.

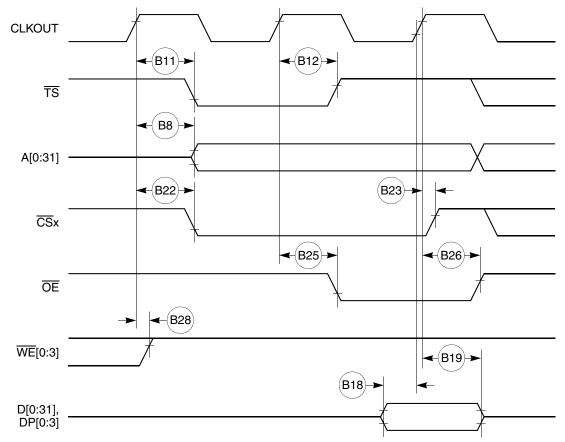


Figure 10. External Bus Read Timing (GPCM Controlled—ACS = 00)



Figure 17 provides the timing for the external bus controlled by the UPM.

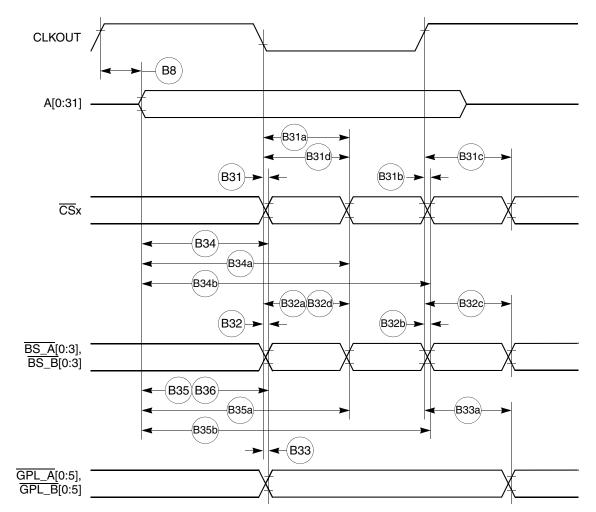


Figure 17. External Bus Timing (UPM Controlled Signals)



Figure 20 provides the timing for the synchronous external master access controlled by the GPCM.

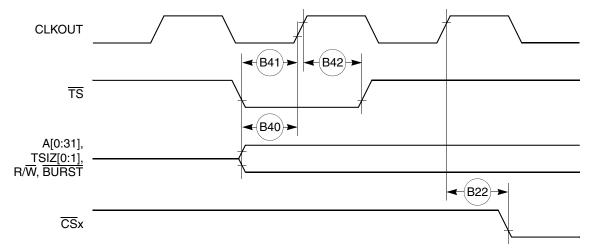


Figure 20. Synchronous External Master Access Timing (GPCM Handled ACS = 00)

Figure 21 provides the timing for the asynchronous external master memory access controlled by the GPCM.

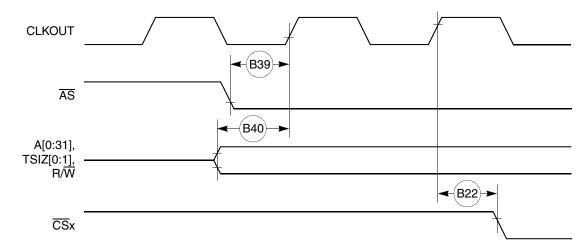


Figure 21. Asynchronous External Master Memory Access Timing (GPCM Controlled—ACS = 00)

Figure 22 provides the timing for the asynchronous external master control signals negation.

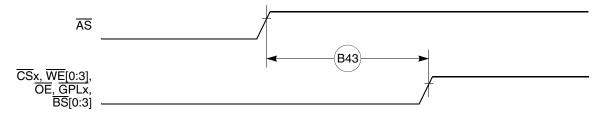


Figure 22. Asynchronous External Master—Control Signals Negation Timing



Table 12 shows the reset timing for the MPC860.

Table 12. Reset Timing

	Observation to the	33 N	1Hz	40 MHz		50 N	1Hz	66 MHz		
Num	Characteristic	Min	Max	Min	Max	Min	Max	Min	Max	Unit
R69	CLKOUT to HRESET high impedance	_	20.00	_	20.00	_	20.00	_	20.00	ns
R70	CLKOUT to SRESET high impedance	_	20.00	_	20.00	_	20.00	_	20.00	ns
R71	RSTCONF pulse width	515.15	_	425.00		340.00	_	257.58	_	ns
R72		_	_	_	_	_	_	_	_	
R73	Configuration data to HRESET rising edge setup time	504.55	_	425.00	_	350.00	_	277.27	_	ns
R74	Configuration data to RSTCONF rising edge setup time	350.00	_	350.00	_	350.00	_	350.00	_	ns
R75	Configuration data hold time after RSTCONF negation	0.00	_	0.00	_	0.00	_	0.00	_	ns
R76	Configuration data hold time after HRESET negation	0.00	_	0.00	_	0.00	_	0.00	_	ns
R77	HRESET and RSTCONF asserted to data out drive	_	25.00		25.00	_	25.00	_	25.00	ns
R78	RSTCONF negated to data out high impedance	_	25.00	_	25.00	_	25.00	_	25.00	ns
R79	CLKOUT of last rising edge before chip three-state HRESET to data out high impedance	_	25.00	_	25.00	_	25.00	_	25.00	ns
R80	DSDI, DSCK setup	90.91	_	75.00	_	60.00	_	45.45	_	ns
R81	DSDI, DSCK hold time	0.00	_	0.00	_	0.00	_	0.00	_	ns
R82	SRESET negated to CLKOUT rising edge for DSDI and DSCK sample	242.42		200.00		160.00	_	121.21	_	ns



Table 16. IDMA Controller Timing (continued)

Num	Observatoristis	All Freq	Unit	
	Characteristic	Min	Max	Unit
42	SDACK assertion delay from clock high	_	12	ns
43	SDACK negation delay from clock low	_	12	ns
44	SDACK negation delay from TA low	_	20	ns
45	SDACK negation delay from clock high	_	15	ns
46	$\overline{\text{TA}}$ assertion to rising edge of the clock setup time (applies to external $\overline{\text{TA}}$)	7	_	ns

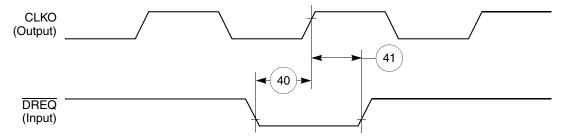


Figure 45. IDMA External Requests Timing Diagram

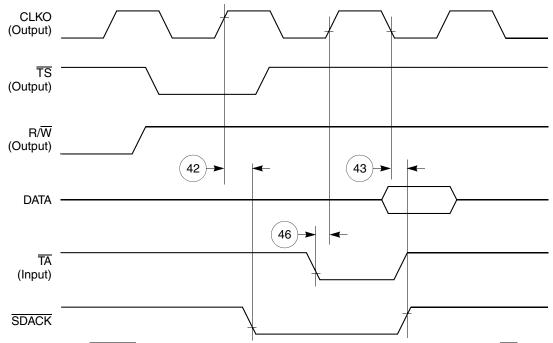


Figure 46. SDACK Timing Diagram—Peripheral Write, Externally-Generated TA



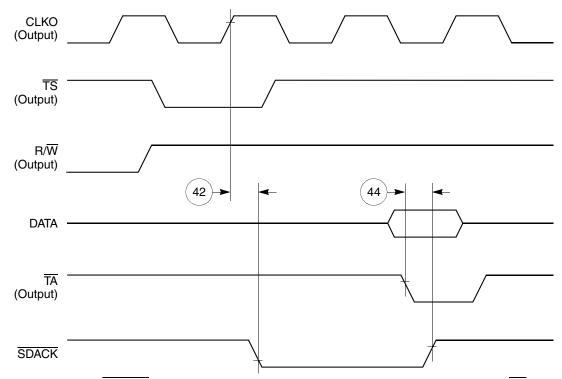


Figure 47. SDACK Timing Diagram—Peripheral Write, Internally-Generated TA

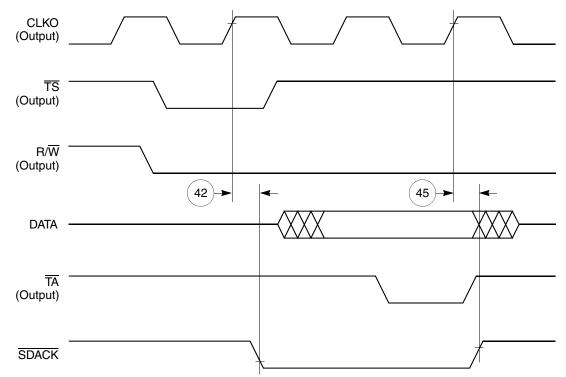


Figure 48. SDACK Timing Diagram—Peripheral Read, Internally-Generated TA



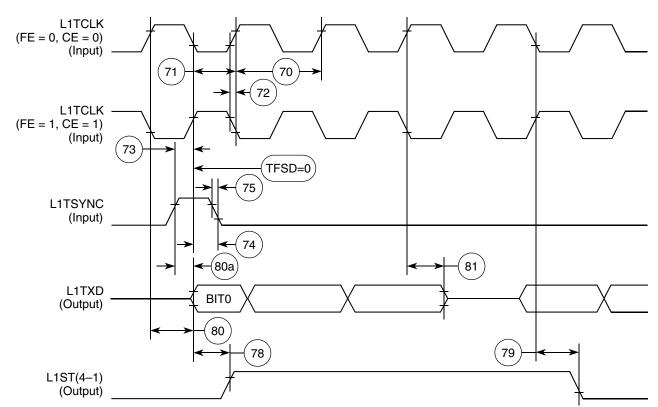


Figure 53. SI Transmit Timing Diagram (DSC = 0)



Table 22. Ethernet Timing (continued)

Num	Chavastaviatia	All Freq	Unit	
	Characteristic	Min	Max	Unit
135	RSTRT active delay (from TCLK1 falling edge)	10	50	ns
136	RSTRT inactive delay (from TCLK1 falling edge)	10	50	ns
137	REJECT width low	1	_	CLK
138	CLKO1 low to SDACK asserted ²	_	20	ns
139	CLKO1 low to SDACK negated ²	_	20	ns

¹ The ratios SYNCCLK/RCLK1 and SYNCCLK/TCLK1 must be greater than or equal to 2/1.

² SDACK is asserted whenever the SDMA writes the incoming frame DA into memory.

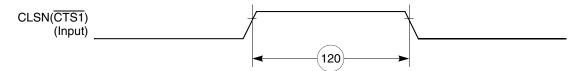


Figure 59. Ethernet Collision Timing Diagram

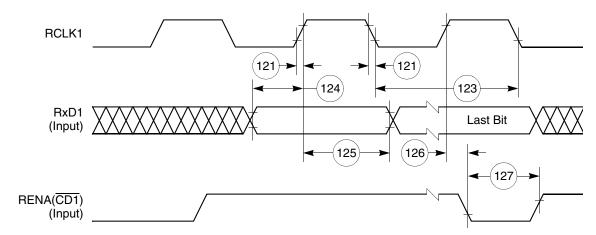


Figure 60. Ethernet Receive Timing Diagram



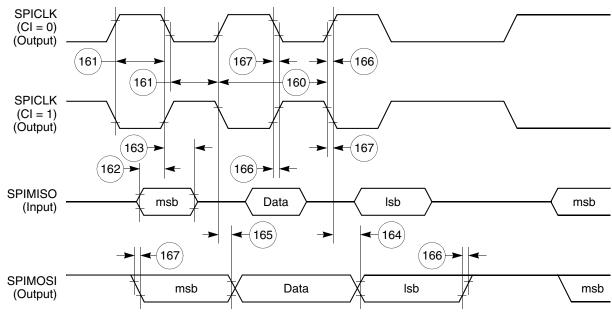


Figure 66. SPI Master (CP = 1) Timing Diagram

11.11 SPI Slave AC Electrical Specifications

Table 25 provides the SPI slave timings as shown in Figure 67 and Figure 68.

Table 25. SPI Slave Timing

Num	Characteristic		uencies	Unit
Nulli	Characteristic	Min	Max	Oille
170	Slave cycle time	2	_	t _{cyc}
171	Slave enable lead time	15	_	ns
172	Slave enable lag time	15	_	ns
173	Slave clock (SPICLK) high or low time	1	_	t _{cyc}
174	Slave sequential transfer delay (does not require deselect)	1	_	t _{cyc}
175	Slave data setup time (inputs)	20	_	ns
176	Slave data hold time (inputs)	20	_	ns
177	Slave access time	_	50	ns



MII Transmit Signal Timing (MII_TXD[3:0], MII_TX_EN, 13.2 MII_TX_ER, MII_TX_CLK)

The transmitter functions correctly up to a MII TX CLK maximum frequency of 25 MHz +1%. There is no minimum frequency requirement. In addition, the processor clock frequency must exceed the MII TX CLK frequency – 1%.

Table 30 provides information on the MII transmit signal timing.

Table 30. MII Transmit Signal Timing

Num	Characteristic	Min	Max	Unit
M5	MII_TX_CLK to MII_TXD[3:0], MII_TX_EN, MII_TX_ER invalid	5	_	ns
M6	MII_TX_CLK to MII_TXD[3:0], MII_TX_EN, MII_TX_ER valid	_	25	
M7	MII_TX_CLK pulse width high	35	65%	MII_TX_CLK period
M8	MII_TX_CLK pulse width low	35%	65%	MII_TX_CLK period

Figure 73 shows the MII transmit signal timing diagram.

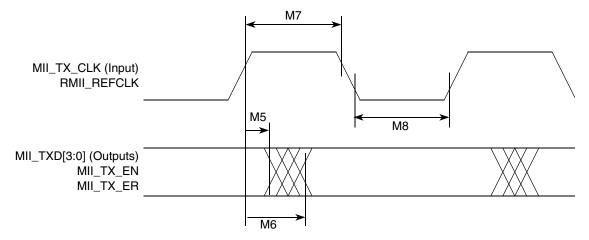


Figure 73. MII Transmit Signal Timing Diagram

MPC860 PowerQUICC Family Hardware Specifications, Rev. 10 68 Freescale Semiconductor



13.3 MII Async Inputs Signal Timing (MII_CRS, MII_COL)

Table 31 provides information on the MII async inputs signal timing.

Table 31. MII Async Inputs Signal Timing

Num	Characteristic	Min	Max	Unit
M9	MII_CRS, MII_COL minimum pulse width	1.5		MII_TX_CLK period

Figure 74 shows the MII asynchronous inputs signal timing diagram.

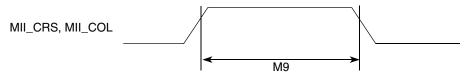


Figure 74. MII Async Inputs Timing Diagram

13.4 MII Serial Management Channel Timing (MII_MDIO, MII_MDC)

Table 32 provides information on the MII serial management channel signal timing. The FEC functions correctly with a maximum MDC frequency in excess of 2.5 MHz. The exact upper bound is under investigation.

Table 32. MII Serial Management Channel Timing

Num	Characteristic	Min	Max	Unit
M10	MII_MDC falling edge to MII_MDIO output invalid (minimum propagation delay)	0	_	ns
M11	MII_MDC falling edge to MII_MDIO output valid (max prop delay)	_	25	ns
M12	MII_MDIO (input) to MII_MDC rising edge setup	10	_	ns
M13	MII_MDIO (input) to MII_MDC rising edge hold	0	_	ns
M14	MII_MDC pulse width high	40%	60%	MII_MDC period
M15	MII_MDC pulse width low	40%	60%	MII_MDC period



Table 34 identifies the packages and operating frequencies available for the MPC860.

Table 34. MPC860 Family Package/Frequency Availability

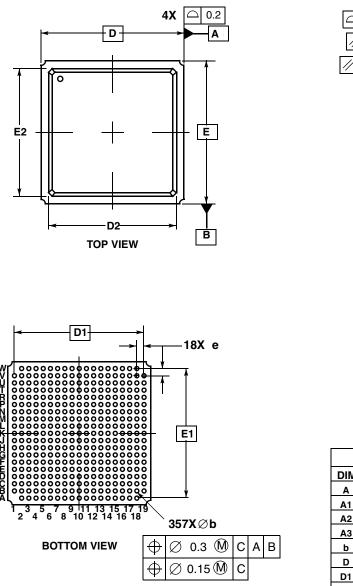
Package Type	Freq. (MHz) / Temp. (Tj)	Package	Order Number
Ball grid array ZP suffix—leaded ZQ suffix—leaded VR suffix—lead-free	leaded 0° to 95°C	ZP/ZQ ¹	MPC855TZQ50D4 MPC860DEZQ50D4 MPC860DTZQ50D4 MPC860ENZQ50D4 MPC860SRZQ50D4 MPC860TZQ50D4 MPC860DPZQ50D4 MPC860PZQ50D4
		Tape and Reel	MPC855TZQ50D4R2 MPC860DEZQ50D4R2 MPC860ENZQ50D4R2 MPC860SRZQ50D4R2 MPC860TZQ50D4R2 MPC860DPZQ50D4R2 MPC855TVR50D4R2 MPC860ENVR50D4R2 MPC860SRVR50D4R2 MPC860SRVR50D4R2
		VR	MPC855TVR50D4 MPC860DEVR50D4 MPC860DPVR50D4 MPC860DTVR50D4 MPC860ENVR50D4 MPC860PVR50D4 MPC860SRVR50D4 MPC860SRVR50D4
	66 0° to 95°C	ZP/ZQ ¹	MPC855TZQ66D4 MPC860DEZQ66D4 MPC860DTZQ66D4 MPC860ENZQ66D4 MPC860SRZQ66D4 MPC860TZQ66D4 MPC860DPZQ66D4 MPC860PZQ66D4
		Tape and Reel	MPC860SRZQ66D4R2 MPC860PZQ66D4R2
		VR	MPC855TVR66D4 MPC860DEVR66D4 MPC860DPVR66D4 MPC860DTVR66D4 MPC860ENVR66D4 MPC860PVR66D4 MPC860SRVR66D4 MPC860SRVR66D4 MPC860TVR66D4



Mechanical Data and Ordering Information

14.3 Mechanical Dimensions of the PBGA Package

Figure 77 shows the mechanical dimensions of the ZP PBGA package.



NOTE

- 1. Dimensions and tolerance per ASME Y14.5M, 1994.
- 2. Dimensions in millimeters.
- Dimension b is the maximum solder ball diameter measured parallel to data C.

	MILLIMETERS		
DIM	MIN MAX		
Α		2.05	
A 1	0.50	0.70	
A2	0.95	1.35	
А3	0.70	0.90	
b	0.60	0.90	
D	25.00 BSC		
D1	22.86 BSC		
D2	22.40	22.60	
е	1.27 BSC		
Е	25.00 BSC		
E1	22.86 BSC		
E2	22.40 22.60		

SIDE VIEW

0.2 C

Figure 77. Mechanical Dimensions and Bottom Surface Nomenclature of the ZP PBGA Package